

CLAIM AMENDMENTS

The following is a complete list of claims. The claims below replace all prior versions of the claims in the application. Please amend claims 1 and 12; and cancel claim 13.

1. (Currently Amended) A method for manufacturing a wafer-level package, comprising:
 - providing a first wafer and a second wafer;
 - removing a portion from the first wafer to form a gasket;
 - forming a pad on the second wafer, the pad projecting from a surface of the second wafer and substantially matching the gasket;
 - interposing bonding material between the gasket and the pad; and
 - bonding the gasket to the pad with the bonding material to create a hermetically sealed environment between the first and second wafers.
2. (Original) The method of claim 1 wherein the first wafer consists of silicon.
3. (Original) The method of claim 2 wherein the gasket is no more than 20 um wide.
4. (Original) The method of claim 3 wherein the gasket is no more than 10 um wide.
5. (Original) The method of claim 3 wherein interposing bonding material includes depositing bonding material on the gasket.
6. (Original) The method of claim 3 wherein interposing bonding material includes depositing bonding material on the pad.
7. (Original) The method of claim 3 wherein the bonding material includes conductive bonding material.
8. (Original) The method of claim 7 wherein the conductive bonding material is a metal selected from the group consisting of gold, gold-tin, tin-lead, and palladium-tin.

9. (Original) The method of claim 3 wherein the bonding material includes non-conductive bonding material.
10. (Original) The method of claim 9 wherein the non-conductive bonding material is a material selected from the group consisting of polyimide, B-staged bisbenzocyclobutene (BCB), and glass.
11. (Original) The method of claim 10 wherein interposing an adhesion promoter between the gasket and the pad occurs after interposing bonding material.
12. (Currently Amended) A method for manufacturing a wafer-level package, comprising:
 - providing a first wafer and a second wafer;
 - forming a pad on the second wafer, the pad having a surface for bonding with substantially matching a gasket of the first wafer, the surface being located a distance away from a surface of the second wafer where the pad is formed;
 - interposing bonding material between the gasket and the pad; and
 - bonding the gasket to the pad with the bonding material to create a hermetically sealed environment between the first and second wafers.
13. Canceled